

ABSTRACT

Semiconductor devices and methods for manufacturing the same in which deterioration of the electrical characteristic is suppressed are described. One method for manufacturing a semiconductor device includes the steps of: forming a first polysilicon layer 32 on a gate dielectric layer 20; forming a silicon nitride layer 92 on the first polysilicon layer 32; forming a second polysilicon layer 94 on the silicon nitride layer 92; forming sidewall spacers; forming an insulation layer 60 that covers the second polysilicon layer 94; planarizing the insulation layer 60 until an upper surface of the second polysilicon layer 94 is exposed; removing the second polysilicon layer 94; removing the silicon nitride layer 92 to form a recessed section 80; and filling a metal layer 34 in the recessed section 80 to form a gate electrode 30 that includes at least the first polysilicon layer 32 and the metal layer 34.